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Research paper



Directional dependency of mechanical properties in gallium phosphide semiconducting material

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Abstract

The aims of this contibution is to investigate the directional dependency of mechanical properties of gallium phosphide (GaP) semiconduct-ing material using the experimental stiffness elastic constants C_{ij} reported in the litterature. These characteristics are visible by analysis and visualization of elastic tensors. The spatial dependencies of the Young's modulus, linear compressibility, shear modulus, and Poisson's ratio in GaP binary compound were calculated and schematized in graphical representations. Data analysis shows that the maximum value E_{max} of Young's modulus was estimated at around 166.7 GPa, while its minimum value E_{min} was estimated at around 102.5 GPa, which gives a ratio of approximately $E_{max}/E_{min} \approx 1.63$, while for the Poisson's ratio v, the maximum value v_{max} of v was estimated at around 0.43, while its minimum value $v_{min} \approx 1.63$, while for the Poisson's ratio v, the maximum value $v_{max}/v_{min} \approx 17.5$. The Debye temperature was also calculated, it is estimated at about 482.4 K, it is in good agreement with the experimental one (493 K) reported in the litterature, and the deviation between these two values is less than 2.2%.

Keywords: Mechanical Properties; Gallium Phosphide; Elastic Anisotropy; Graphical Representation.

1. Introduction

The elastic constants are important for determining the structural and thermal properties as well as the mechanical stability of materials. Furthermore, these quantities provide much information on the mechanical behaviour of the material to both the intrinsic and extrinsic forces applied to its crystal structure [1]. Mechanical stability was obtained by confirming the elastic constants C_{ij} [1].

Different theoretical approaches [1-22] and experimental technics [23-25] were used to study the elastic constants, thermel properties and some other physical properties of materials.

Using first-principle calculations, Moin and co-authors [6] have investigated structural, electronic, mechanical, optical, and thermodynamic features of promising (La, In)-doped AlSb for optoelectronic applications. Daoud [7] has investigated the mechanical behavior of aluminum phosphide under high pressure, while in other work Daoud and co-authors [20] have investigated the elastic constants and optical phonon frequencies of BX (X= P, As, and Sb) semiconductors using semi-empirical approach. Maaitah [21] has investigated the mechanical, optical, and lattice vibrational properties of gallium antimonide (GaSb) semiconductor under the influence of temperature using the empirical pseudopotential method (EPM), while Mezouar and co-authors [22] have investigated the mechanical properties of $B_xAl_{1-x}Sb$ ternary semiconducting alloys.

Weir [26] has investigated the high pressure phase transitions in the II-VI and III-V compounds, barium selenide, barium sulfide, barium oxide, gallium antimonide, gallium arsenide, and gallium phosphide, while Bouarissa and co-authors [27] have reported on the pressureeffects on band structure and chemical bonding of GaP semiconducting compound using the empirical pseudopotential method (EPM). Benalia et al. [28] have studied the band gap behavior of scandium aluminum phosphide and scandium gallium phosphide ternary alloys and superlattices, Benamrani et al. [29] have studied structural, elastic and thermodynamic properties of ScP compound, while Rekab-Djabri et al. [30] have studied the ground state parameters, electronic properties and elastic constants of CaMg₃ intermetallic compound. In the present contribution, we investigate the spatial dependencies of some engeniring moduli, especialy: the Young's modulus, linear compressibility, shear modulus, and Poisson's ratio in GaP binary semiconducting compound based on the experimental stiffness elastic constants C_{ij} reported in the litterature [31].

2. Theory and discussion of the results

In the case of cubic crystals, there are only three independent constants (C_{11} , C_{12} and C_{44}) that characterize the material [32-35]. For an arbitrary crystallographic direction m, the Young modulus E of single crystal may be given by this relationship [31]:



(1)

$$E^{-1} = S_{11} - 2(S_{11} - S_{12} - 0.5S_{44})(m_1^2 m_2^2 + m_2^2 m_3^2 + m_1^2 m_3^2)$$

Where S_{ij} are the compliance elastic constants and the m_i are the cosines of the direction m. The Young modulus E for the direction of the cube axes $\langle 100 \rangle$ is readily given by: E = 1/S₁₁[31].

Using the experimental elastic constants C_{ij} ($C_{11} = 140.5$ GPa, $C_{12} = 62.03$ GPa, and $C_{44} = 70.33$ GPa) reported in the litterature [31], and based on the expression describing the direction dependence of the Young's modulus of crystals [31] and the procedure presented by Gaillac et al. [18], the values obtained for the Young's modulus E as a function of the direction for the GaP semiconductor are presented in 2 dimensions (2D) and 3 dimensions (3D) in Figure 1 (A) and (B), respectively. The degree of anisotropy is dependent on the deviation of geometrical body (3D) from the spherical shape in this case, represented in a 2D shape. Data analysis shows that the maximum value E_{max} of Young's modulus was estimated at around 166.7 GPa (within (110) crystallographic plane and in [111] direction) [31], while its minimum value E_{min} was estimated at around 102.5 GPa (both within (100) crystallographic plane and in [001] direction, an within (110) crystallographic plane and in [001] direction) [31], which gives a ratio of approximately $E_{max}/E_{min} \approx 1.63$.

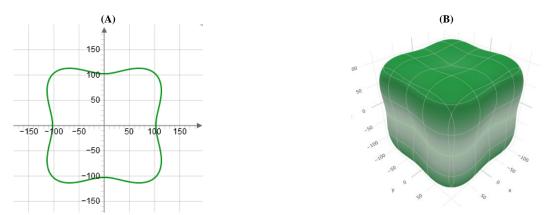


Fig. 1: The Spatial Dependency of Young Modulus in GaP Binary Compound: (A) in XY, XZ and YZ Planes, (B) in 3 Dimensions (3D).

The linear compressibility $\beta = 1/(C_{11} + 2C_{12})$ [31]. The implication of the previous definition is that a value of unity corresponds to the isotropic compressibility. The values obtained for the linear compressibility β as a function of the direction for the GaP binary compound are represented in 2 dimensions (2D) in Figure 2 (A). Data analysis shows that the maximum value β_{max} of β is equal to its minimum value β_{min} which is estimated at around 3.78 TPa⁻¹[31]. Since $\beta_{max} = \beta_{min}$ which gives the ratio $\beta_{max}/\beta_{min} = 1$. In order to understand the spatial dependency of the linear compressibility, the values obtained for the linear compressibility β as a function of the direction for GaP binary compound are represented in 3 dimensions (3D) in Figure 2 (B).

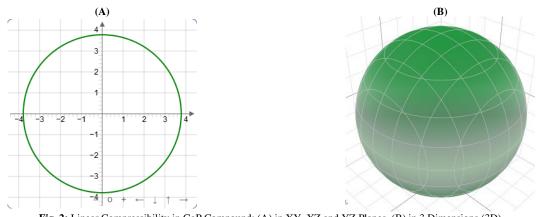


Fig. 2: Linear Compressibility in GaP Compound: (A) in XY, XZ and YZ Planes, (B) in 3 Dimensions (3D).

The values obtained for the shear modulus G as a function of the direction for GaP binary compound are presented in 2 dimensions (2D) and 3 dimensions (3D) in Figure 3 (A) and (B), respectively. A perfect circle (blue colour) represents the isotropy of the crystal structure plane; otherwise, it demonstrates the degree of anisotropy. Data analysis shows that the maximum value G_{max} of the linear compressibility G was estimated at around 70.33 GPa, while the minimum value G_{min} was estimated at around 39.24 GPa, which gives a ratio of approximately $G_{max}/G_{min} = 1.79$. Unfortunately, to our knowledge, no theoretical values or experimental data on G_{min} and G_{max} are available to make comparison. Thus, further theoretical predictions and experimental investigations are significantly needed.

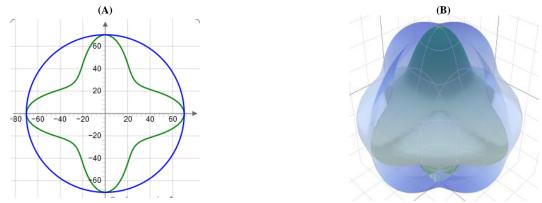


Fig. 3: The Spatial Dependency of Shear Modulus G in GaP Compound: (A) in XY, XZ and YZ Planes, (B) in 3 Dimensions (3D).

For an arbitrary crystallographic direction m and another perpendicular direction n, the Poisson's ratiou is given by this relation [31]:

$$v = -\frac{S_{12} + (S_{11} - S_{12} - 0.5S_{44})(m_1^2 n_1^2 + m_2^2 n_2^2 + m_3^2 n_3^2)}{S_{11} - 2(S_{11} - S_{12} - 0.5S_{44})(m_1^2 m_2^2 + m_2^2 m_3^2 + m_1^2 m_3^2)}$$
(2)

where S_{ij} are the elastic compliance, the m_i are the cosines of the direction m and the n_i are the cosines of the direction n. Using the experimental elastic constants C_{ij} reported in the litterature [31], the values obtained for the Poisson's ratiov as a function of the direction for the GaP binary compound are represented in 2 dimensions (2D) and 3 dimensions (3D) in Figure 4 (A) and (B), respectively. Data analysis shows that for the Poisson's ratio v, the maximum value v_{max} of v was estimated at around 0.43 (within (100) crystallographic plane and in m = [010] and n = [001] directions) [31], while its minimum value v_{min} was estimated at around 0.025 (within (100) crystallographic plane and in m = [011] and $n = [0\overline{1}1]$ directions) [31], which gives a ratio $v_{max}/v_{min} \approx 17.5$.

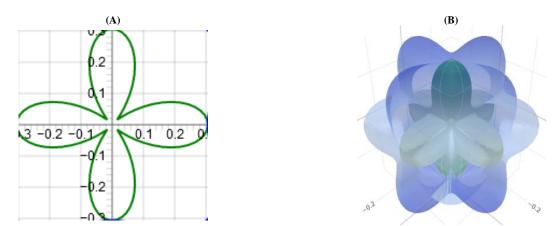


Fig. 4: The Spatial Dependency of Poisson's Ratio in GaP Compound: (A) in XY, XZ, YZ and Planes, (B) in 3 Dimensions (3D).

If the second-order elastic stiffness constants C_{ij} and the mass density ρ of the crystal areknown, it is possible to predict the acoustic sound velocities and the Debye temperature θ_D of materials [36, 37]. Many researchers have extensively employed ab initio methods to investigate the elastic constants C_{ij} and structural, electronic and piezoelectric properties of materials [38-54]. Bioud [54] has used the elastic constants C_{ij} to calculate the wave velocities andthe Debye temperature of CuX (X = Cl, Br) binary compounds Blackman's [55] proposed a formula which is usually used to predict the θ_D of a material from its elastic constants C_{ij} . In cubic systems, θ_D can also be expressed in terms of the elastic constants C_{ij} and the mass density ρ by the following expression [56-59]:

$$\theta_D^3 = \frac{3.15}{8\pi} \left(\frac{h}{k}\right)^3 \left(\frac{n}{\rho^{3/2} V_a}\right) (C_{11} - C_{12})^{1/2} (C_{11} + C_{12} + 2C_{44})^{1/2} (C_{44})^{1/2}$$
(3)

where h is the Planck's constant, k is the Boltzmann constant, n is the number of atoms in unit cell of volume V_a , and ρ is the density. Using the experimental elastic constants C_{ij} (C_{11} = 140.5 GPa, C_{12} = 62.03 GPa, and C_{44} = 70.33 GPa) and the lattice constant (a = 5.4508 Å) reported in the litterature [31], and using the formula of Eq. (3), the calculated value of θ_{Dis} estimated to be about: 482.4 K. The obtained value is in good agreement with the experimental one (493 K) quoted by Adachi [31], the deviation between these two values is estimated to be less than 2.2%.

The concept of the Debye frequency w_D , which is defined as the maximum vibrational frequency of a given mode in a crystal is of fundamental importance in the heat transport in a lattice [60]. For compounds with rocksalt, diamond and zincblende structures, the Debye frequency w_D retated to θ_D as follows: $w_D = 16.5374 \times 10^9 \theta_D$ [60]. For GaP compound, the calculated value of w_D is about: 8 THz.

The acoustic impedance (Z) has been analyzed by the following equation $Z = (\rho G)^{1/2}$ [14], [61], [62], where G is the shear modulus and is the mass density. High values of the shear modulus G and the mass density ρ result in high acoustic impedance [14, 61]. Our obtained value of the acoustic impedance Z for GaP compound is estimated to be about: 15.16×10^6 Rayl. Unfortunately, to the best of our knowledge, there is no other data available in the literature on Z for GaP to compare with our results.

3. Conclusion

Using the experimental stiffness elastic constants C_{ij} reported in the litterature [31], we studied the spatial dependencies of the Young's modulus, linear compressibility, shear modulus, and Poisson's ratio in GaP semiconducting compound. The program used [18] detect the input structure's crystal symmetry and test the mechanical stability of the crystal. Data analysis shows that the maximum value E_{max} of Young's modulus was estimated at around 166.7 GPa (within (110) crystallographic plane and in [111] crystallographic direction) [31], while its minimum value E_{min} was estimated at around 102.5 GPa (for both within (100) crystallographic plane and in [001] direction, an within (110) crystallographic plane and in [001] crystallographic direction) [31], which gives $E_{max}/E_{min} \approx 1.63$, while for the Poisson's ratio v, the maximum value v_{max} of v was estimated at around 0.43 [31], while its minimum value $v_{min} \approx 17.5$. This result indicates that gallium phosphide (GaP) semiconducting material exhibits a large anisotropy on the Poisson's ratio v. Furthermore, the Debye temperature and the acoustic impedance of GaP material are computed.

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